

# NCE P-Channel Enhancement Mode Power MOSFET

## Description

The NCE60P55K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge .This device is well suited for high current load applications.

#### **General Features**

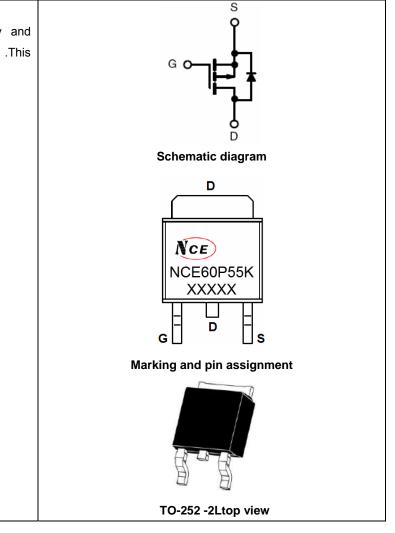
- V<sub>DS</sub> =-60V,I<sub>D</sub> =-55A
  R<sub>DS(ON)</sub> <28mΩ @ V<sub>GS</sub>=-10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

## Application

- High side switch for full bridge converter
- DC/DC converter for LCD display

#### 100% UIS TESTED!

**100% ΔVds TESTED!** 



#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P55K	NCE60P55K	TO-252-2L	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25<sup>°</sup>Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	-55	А
Drain Current-Continuous(T <sub>C</sub> =100 ℃)	I <sub>D</sub> (100℃)	-24.8	А
Pulsed Drain Current	I <sub>DM</sub>	-220	А
Maximum Power Dissipation	PD	110	W
Derating factor		0.73	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	273	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C



## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.36	°C/W	]
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## Electrical Characteristics (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

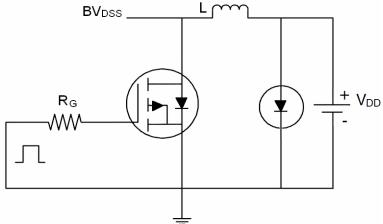
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	····					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	····					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-2	-2.6	-3.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-	23	28	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =-5V,I <sub>D</sub> =-20A	-	25	-	S
Dynamic Characteristics (Note4)			·			•
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V, F=1.0MHz	-	3016.8	-	PF
Output Capacitance	Coss		-	180	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	126	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	12	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =-30V, R <sub>L</sub> =1.5 $\Omega$ ,	-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V,R <sub>G</sub> =3Ω	-	38	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	15	-	nS
Total Gate Charge	Qg		-	49.8		nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-30,I <sub>D</sub> =-20A, V <sub>GS</sub> =-10V	-	10.6		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> 10V	-	13.6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-20A	-		-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-55	А
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =- 20A	-	47		nS
Reverse Recovery Charge	Qrr	di/dt = -100A/µs <sup>(Note3)</sup>	-	53		nC

#### Notes:

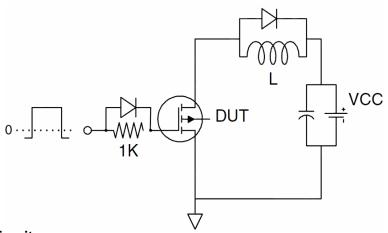
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition: Tj=25 $^\circ\!\mathrm{C}$ ,V<sub>DD</sub>=-20V,V<sub>G</sub>=-10V,L=0.5mH,Rg=25\Omega



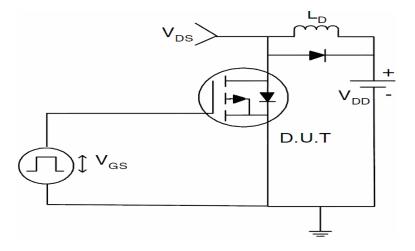
# Test Circuit 1) E<sub>AS</sub> Test Circuit



# 2) Gate Charge Test Circuit

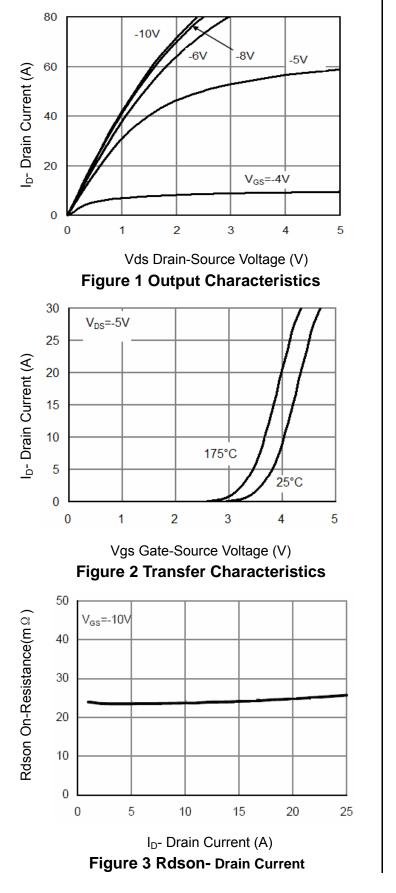


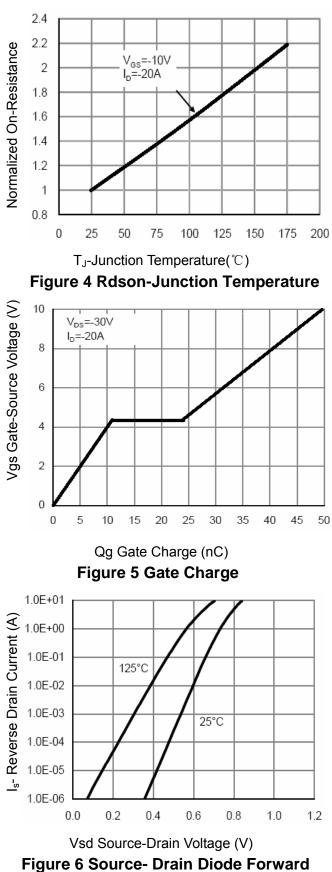
3) Switch Time Test Circuit





# **Typical Electrical and Thermal Characteristics (Curves)**

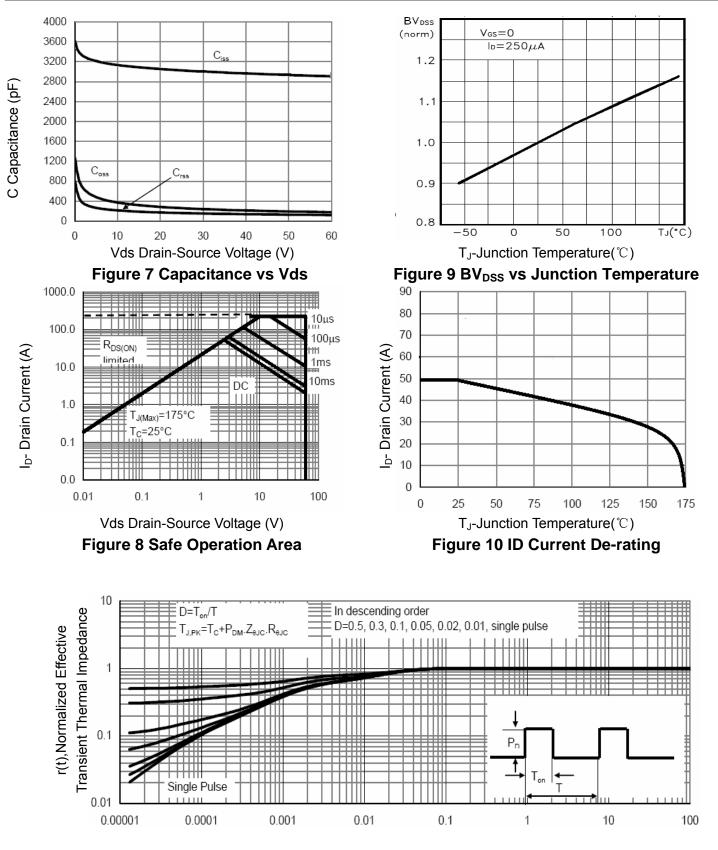






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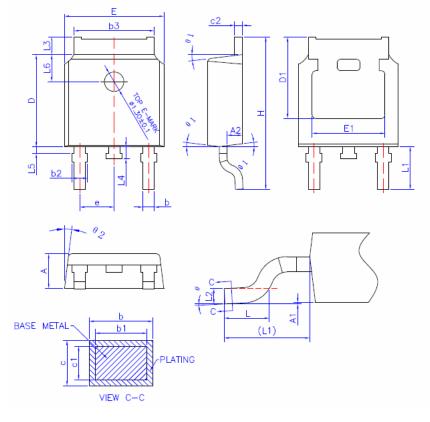
# NCE60P55K



Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



# TO-252 Package Information



#### COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX		
А	2.20	2.30	2.38		
A1	0	—	0,10		
A2	0,90	1,01	1,10		
b	0.72	—	0.85		
b1	0.71	0.76	0.81		
b2	0,72	—	0,90		
b3	5,13	5,33	5,46		
с	0.47	—	0.60		
c1	0.46	0.51	0.56		
c2	0,47	—	0,60		
D	6.00	6,10	6,20		
D1	5.25	—			
E	6.50	6.60	6.70		
E1	4,70	—			
е	2,186	2,286	2,386		
Н	9.80	10.10	10.40		
L	1.40	1.50	1.70		
L1	2	2,90 REF			
L2	0.508 BSC				
L3	0.90	—	1.25		
L4	0.60	0.80	1.00		
L5	0,15	—	0,75		
L6	1.80 REF				
θ	0°	—	8°		
θ1	5°	7°	9°		
θ2	5°	7°	9°		



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